

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:
SERIAL NO.
FILING DATE:
INVENTION:

R. Ugajin
not yet assigned
April 2, 2002
FRACTAL STRUCTURE AND ITS FORMING METHOD

ATTORNEY DOCKET NO. 9794353-0020
GROUP ART UNIT: not yet assigned
EXAMINER: not yet assigned

#2

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL LETTER

COMMISSIONER OF PATENTS
Washington, D.C. 20231

Sir:

Submitted herewith is an Information Disclosure Statement for consideration in the above-identified application. This Information Disclosure Statement is submitted:

- ☒ Within 3 months (1) of filing date of a national application; (2) of date of entry of the national stage as set forth in 37 C.F.R. §1.491 in an international application; or (3) before the mailing date of a first Office Action on the merits, whichever occurs last. (No fee is required.)
- ☐ After the mailing date of a first Office Action but before (1) mailing of a final action under 37 C.F.R. §1.113; or (2) mailing of a notice of allowance under §1.311, whichever occurs first.
- ☐ Payment for the fee set forth in 37 C.F.R. §1.17(p) accompanies this submission; or
- ☐ The certification specified in 37 C.F.R. §1.97(e) is made below. (No fee is required.)
- ☐ After the mailing of (1) a final action under 37 C.F.R. §1.113; or (2) a notice of allowance under 37 C.F.R. §1.311 whichever occurs first, but before payment of the issue fee. The certification specified in 37 C.F.R. §1.97(e) is made below. The Commissioner hereby is petitioned to consider the Information Disclosure Statement accompanying this submission. Payment for the Petition fee set forth in 37 C.F.R. §1.17(i)(1) accompanies this submission.
- ☐ The undersigned counsel for applicant(s) hereby certifies each item of information identified in the Information Disclosure Statement was first cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.
- ☐ The undersigned counsel for applicant(s) hereby certifies that no item of information contained in the Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart foreign application, or to the knowledge of the undersigned, after making reasonable inquiry, was known to any individual designated in 37 C.F.R. §1.56(c) more than three months prior to the filing of this Information Disclosure Statement.
- ☐ A check in the amount of \$_____ to cover any required fee is enclosed.
- ☒ The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Account No. 19-3140. *A duplicate copy of this sheet is enclosed for this purpose.*

Very respectfully,

SONNENSCHN NATH & ROSENTHAL

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CERTIFICATE OF MAILING

I hereby certify that this Information Disclosure Statement is being deposited with the United States Postal Service as U.S. Express Mail, Label No. EL370088458US to Box PCT, Commissioner of Patents, Washington, DC 20231 on

4/2/02

Ellen Hogan
Jo Ellen Hogan

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Box PCT
Commissioner for Patents
Washington, DC 20231

S I R:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the references identified on the attached PTO-1449 form, copies of which are enclosed herewith in accordance with 37 C.F.R. §1.98, be made during the course of examination of the above-referenced application for United States Letters Patent.

I. SUBMITTED UNITED STATES PATENT REFERENCES

<u>Reference</u>	<u>Number</u>	<u>Patentee</u>	<u>Issue Date</u>
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II. SUBMITTED FOREIGN PATENT REFERENCES

<u>Reference</u>	<u>Number</u>	<u>Country</u>	<u>Date of Publication</u>
B1	11-195801	JP	21 July 1999
B2	2001-118379	JP	27 April 2001

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III OTHER DOCUMENTS

<u>Reference</u>	<u>Title/Author</u>	<u>Date of Publication</u>
C1	H. Isshiki, K. Tanaka and T. Kimura, "Conduction subband formation in (GaSa)m(GaP)n FRACTAL structured atomic-layer-superlattice grown By atomic layer epitaxy", Proc. of the 24 th International Conference on The Physics of Semiconductors, CD-ROM File No. 0948, World Scientific Publishing Co.	1999
C2	R. Ugajin, "Composite nanomaterials based on fractal-shaped structures", Physics Letters A, 227, Pages 267 to 272.	2000

IV. EXPLANATION OF RELEVANCE

The references were cited in the Japanese Patent Office Search Report of November 13, 2001, in counterpart PCT/JP01/07248. A copy of the Search Report is submitted herewith.

Submitted by,



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